74HC4520-Q100; 74HCT4520-Q100

Dual 4-bit synchronous binary counter

Rev. 1 — 4 December 2014

Product data sheet

1. General description

The 74HC4520-Q100; 74HCT4520-Q100 are dual 4-bit internally synchronous binary counters with two clock inputs (nCP0 and nCP1). They have buffered outputs from all 4 bit positions (nQ0 to nQ3), and an asynchronous master reset input (nMR). The counter advances on either the LOW-to-HIGH transition of nCP0 when nCP1 is HIGH. It also advances on the HIGH-to-LOW transition of nCP1 if nCP0 is LOW. Either nCP0 or nCP1 may be used as the clock input to the counter. The other clock input may be used as a clock enable input. A HIGH on nMR resets the counter (nQ0 to nQ3 = LOW) independent of nCP0 and nCP1. Inputs include clamp diodes. It enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Complies with JEDEC standard no. 7A
- Input levels:
 - ◆ For 74HC4520-Q100: CMOS level
 - ◆ For 74HCT4520-Q100: TTL level
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

3. Applications

- Multistage synchronous counting
- Multistage asynchronous counting
- Frequency dividers

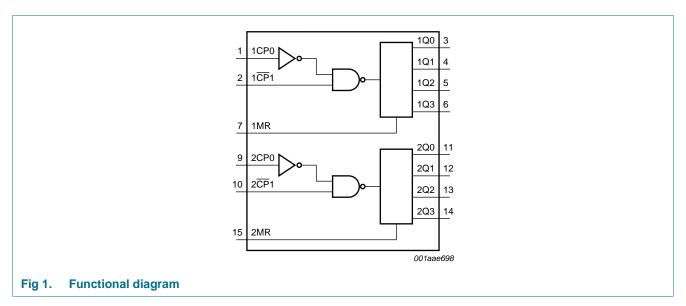


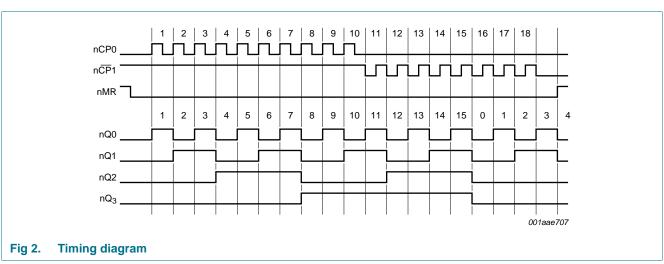
4. Ordering information

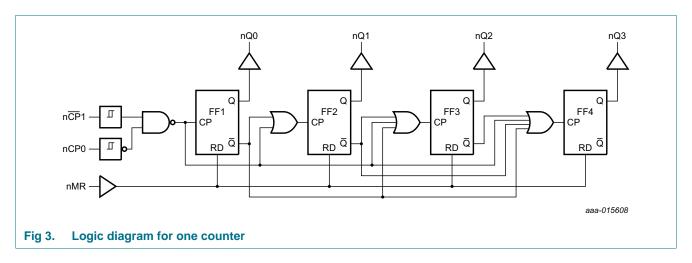
Table 1. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74HC4520D-Q100	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads;	SOT109-1					
74HCT4520D-Q100	-		body width 3.9 mm						
74HC4520PW-Q100	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1					

5. Functional diagram

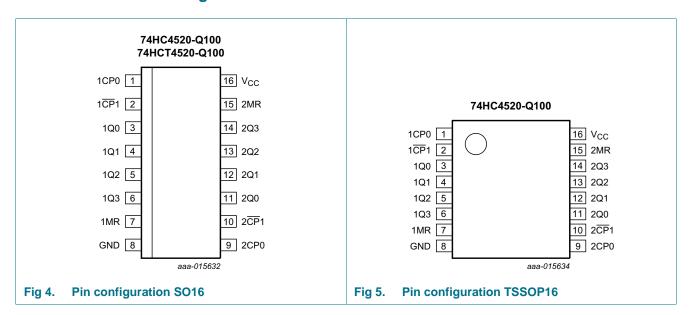






6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1CP0, 2CP0	1, 9	clock input (LOW-to-HIGH edge-triggered)
1CP1, 2CP1	2, 10	clock input (HIGH-to-LOW edge-triggered)
1Q0 to 1Q3	3, 4, 5, 6	output
1MR, 2MR	7, 15	asynchronous master reset input (active HIGH)
GND	8	ground (0 V)
2Q0 to 2Q3	11, 12, 13, 14	output
V _{CC}	16	supply voltage

74HC_HCT4520_Q100

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7. Functional description

Table 3. Function table[1]

nCP0	nCP1	nMR	Mode
↑	Н	L	counter advances
L	↓	L	counter advances
↓	X	L	no change
X	\uparrow	L	no change
↑	L	L	no change
Н	\	L	no change
X	X	Н	nQ0 to nQ3 = LOW

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; ↑ = positive-going transition; ↓ = negative-going transition.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		- · · · · · · · · · · · · · · · · · · ·				-
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+7.0	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		-	±20	mA
I _{OK}	output clamping current	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V}$		-	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } V_{CC} + 0.5 \text{ V}$		-	±25	mA
I _{CC}	supply current			-	50	mA
I _{GND}	ground current			-50	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	SO16 and TSSOP16 packages	[1]	-	500	mW

^[1] For SO16 package: above 70 °C the value of P_{tot} derates linearly at 8 mW/K. For TSSOP16 package: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC4520-Q100			74H0	CT4520-0	Q100	Unit
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC452	20-Q100							1		
V_{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}	•	•						
	output voltage	$I_O = -20 \mu A$; $V_{CC} = 2.0 \text{ V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -4.0$; $V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -5.2$; $V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_O = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μА
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80.0	-	160.0	μА
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	–40 °C to	+125 °C	Unit	
			Min	Тур	Max	Min	Max	Min	Max		
74HCT4	520-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V	
V_{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V	
V _{OH}		$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$		1						1	
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V	
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V	
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$									
		I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V	
		I _O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V	
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80.0	-	160.0	μΑ	
ΔI_{CC}	additional	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$;	other in	puts at	V _{CC} or	GND; V _C	_C = 4.5 V	to 5.5 V; I	O = 0 A	•	
	supply current	pin nCP0, nCP1	-	80	288	-	360	-	392	μΑ	
		pin nMR	-	150	540	-	675	-	735	μΑ	
C _I	input capacitance		-	3.5	-	-	-	-	-	pF	

11. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see Figure 7.

Symbol	Parameter	Conditions	25 °C		–40 °C to	+85 °C	-40 °C to +125 °C		Unit	
			Min	Тур	Max	Min	Max	Min	Max	
74HC452	20-Q100			•						
t _{pd}	propagation	nCP0 to nQn; see Figure 6 [1]								
	delay	V _{CC} = 2.0 V	-	77	240	-	300	-	360	ns
		V _{CC} = 4.5 V	-	28	48	-	60	-	72	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	24	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	22	41	-	51	-	61	ns
		nCP1 to nQn; see Figure 6 [1]								
		V _{CC} = 2.0 V	-	77	240	-	300	-	360	ns
		V _{CC} = 4.5 V	-	28	48	-	60	-	72	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	24	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	22	41	-	51	-	61	ns

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit, see Figure 7.

Symbol	Parameter	Conditions		25 °C		–40 °C to	+85 °C	-40 °C to +125 °C		Unit	
			Min	Тур	Max	Min	Max	Min	Max		
t _{PHL}	HIGH to LOW	nMR to nQn; see Figure 6									
	propagation	V _{CC} = 2.0 V	-	44	150	-	190	-	225	ns	
	delay	V _{CC} = 4.5 V	-	16	30	-	38	-	45	ns	
		V _{CC} = 5.0 V; C _L = 15 pF	-	13	-	-	-	-	-	ns	
		V _{CC} = 6.0 V	-	13	26	-	33	-	38	ns	
t _t	transition	nQn; see Figure 6 [2]									
	time	V _{CC} = 2.0 V	-	19	75	-	95	-	110	ns	
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns	
		V _{CC} = 6.0 V	-	6	13	-	16	-	19	ns	
t _W	pulse width	nCP0, nCP1 HIGH or LOW; see Fi	gure 6								
		V _{CC} = 2.0 V	80	22	-	100	-	120	-	ns	
		V _{CC} = 4.5 V	16	8	-	20	-	24	-	ns	
		V _{CC} = 6.0 V	14	6	-	17	-	20	-	ns	
		nMR HIGH; see Figure 6									
		V _{CC} = 2.0 V	120	39	-	150	-	180	-	ns	
		V _{CC} = 4.5 V	24	14	-	30	-	36	-	ns	
		V _{CC} = 6.0 V	20	11	-	26	-	31	-	ns	
t _{rec}	recovery time										
		V _{CC} = 2.0 V	0	-28	-	0	-	0	-	ns	
		V _{CC} = 4.5 V	0	-10	-	0	-	0	-	ns	
		V _{CC} = 6.0 V	0	-8	-	0	-	0	-	ns	
t _{su}	set-up time	nCP0 to nCP1; nCP1 to nCP0; see Figure 6									
		V _{CC} = 2.0 V	80	14	-	100	-	120	-	ns	
		V _{CC} = 4.5 V	16	5	-	20	-	24	-	ns	
		V _{CC} = 6.0 V	14	4	-	17	-	20	-	ns	
f _{max}	maximum	nCP0, nCP1; see Figure 6						1	-		
	frequency	V _{CC} = 2.0 V	6	19	-	4.8	-	4	-	MHz	
		V _{CC} = 4.5 V	30	58	-	24	-	20	-	MHz	
		V _{CC} = 5.0 V; C _L = 15 pF	-	68	-	-	-	-	-	MHz	
		V _{CC} = 6.0 V	35	69	-	28	-	24	-	MHz	
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}; V_{CC} = 5 \text{ V};$ $f_i = 1 \text{ MHz}$	-	29	-	-	-	-	-	pF	
74HCT45	520-Q100										
t _{pd}	propagation	nCP0 to nQn; see Figure 6 [1]									
ρū	delay	V _{CC} = 4.5 V	-	28	53	-	66	-	80	ns	
		V _{CC} = 5.0 V; C _L = 15 pF	-	24	-	-	-	-	-	ns	
		$v_{CC} = 3.0 \text{ V}, C_L = 13 \text{ pr}$ $\overline{\text{CP1}}$ to nQn; see Figure 6 11									
		V _{CC} = 4.5 V	-	25	53	-	66	-	80	ns	
		$V_{CC} = 5.0 \text{ V; } C_L = 15 \text{ pF}$	_	24	-	_	-		1	ns	

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 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit, see Figure 7.

Symbol	Parameter	Conditions		25 °C		-40 °C to	+85 °C	-40 °C to +125 °C		Unit
				Тур	Max	Min	Max	Min	Max	
t _{PHL}	HIGH to LOW	nMR to nQn; see Figure 6								-
	propagation delay	V _{CC} = 4.5 V	-	16	35	-	44	-	53	ns
	delay	V _{CC} = 5.0 V; C _L = 15 pF	-	13	-	-	-	-	-	ns
t _t	transition	nQn; see Figure 6								
	time	V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
t _W	pulse width	nCP0, nCP1 HIGH or LOW; see Fi	gure 6	<u> </u>						
		V _{CC} = 4.5 V	20	10	-	25	-	30	-	ns
		nMR HIGH; see Figure 6								
		V _{CC} = 4.5 V	20	12	-	25	-	30	-	ns
t _{rec}	recovery time	nMR to nCP0, nCP1; see Figure 6								
		V _{CC} = 4.5 V	0	-8	-	0	-	0	-	ns
t _{su}	set-up time	nCP0 to nCP1; nCP1 to nCP0; see	Figur	<u>e 6</u>						
		V _{CC} = 4.5 V	16	6	-	20	-	24	-	ns
f _{max}	maximum	nCP0, nCP1; see Figure 6								
	frequency	V _{CC} = 4.5 V	30	58	-	24	-	20	-	MHz
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	64	-	-	-	-	-	MHz
C _{PD}	power dissipation capacitance	$V_{I} = GND \text{ to } V_{CC} - 1.5 \text{ V};$ $V_{CC} = 5 \text{ V}; f_{i} = 1 \text{ MHz}$	-	24	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \sum (C_L \times V_{CC}{}^2 \times f_o)$$
 where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

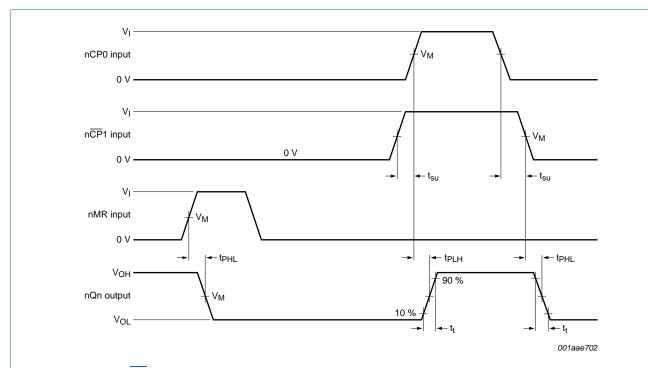
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

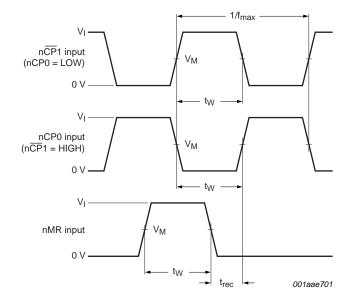
N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = sum of outputs.$

12. Waveforms



a. nCP0 and $n\overline{CP1}$ set-up times, propagation delays and output transition times



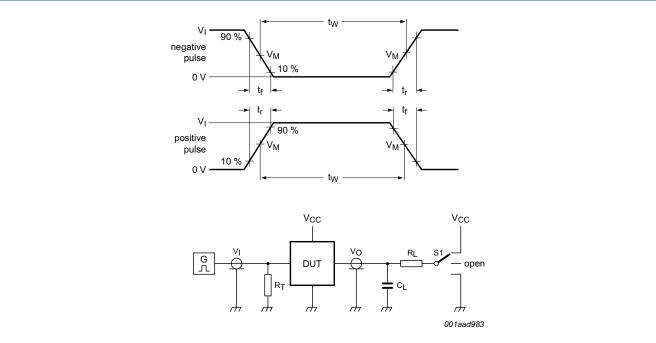
b. nMR recovery time, minimum nCP0, nCP1, nMR pulse widths and maximum frequency Measurement points are given in Table 8.

The logic levels V_{OH} and V_{OL} are typical output voltage levels that occur with the output load.

Fig 6. Waveforms showing measurements for switching times

Table 8. Measurement points

Туре	Input	Output	
	V _M	V _I	V _M
74HC4520-Q100	$0.5 \times V_{CC}$	GND to V _{CC}	$0.5 \times V_{CC}$
74HCT4520-Q100	1.3 V	GND to 3 V	1.3 V



Test data is given in Table 9.

Test circuit definitions:

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator

C_L = Load capacitance including jig and probe capacitance

 R_L = Load resistance.

S1 = Test selection switch

Fig 7. Test circuit for measuring switching times

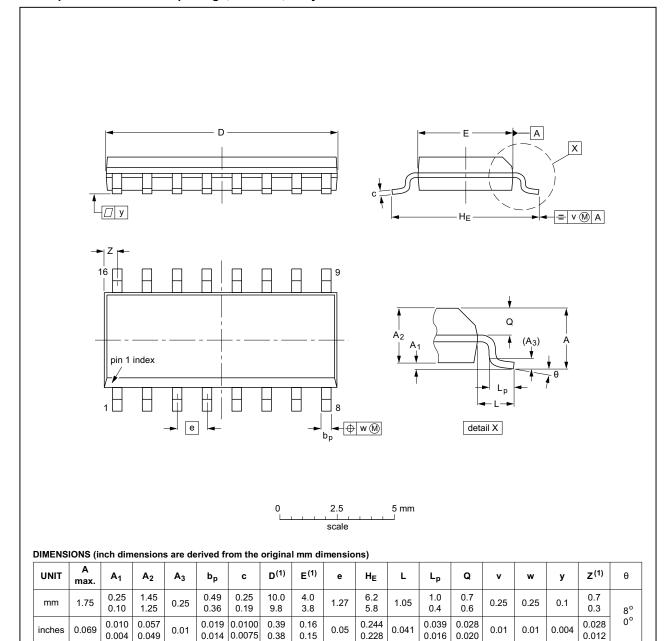
Table 9. Test data

Туре	Input		Load	S1 position	
	V _I	t _r , t _f	CL	R _L	t _{PHL} , t _{PLH}
74HC4520-Q100	V _{CC}	6 ns	15 pF, 50 pF	1 kΩ	open
74HCT4520-Q100	3 V	6 ns	15 pF, 50 pF	1 kΩ	open

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

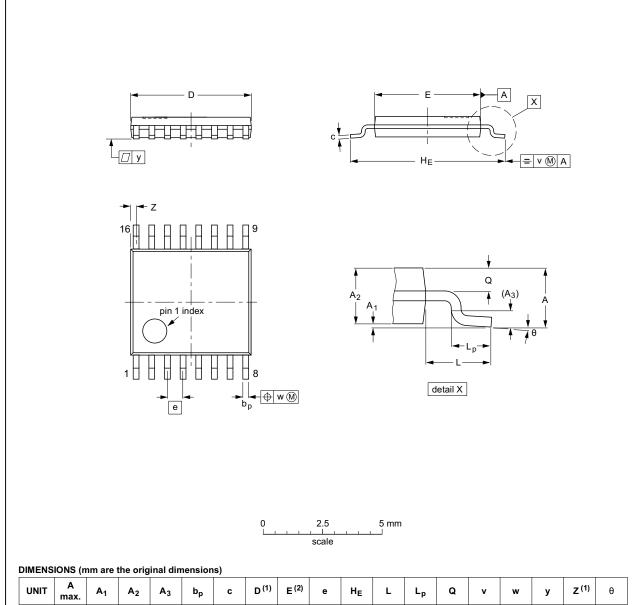
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012				99-12-27 03-02-19	

Fig 8. Package outline SOT109-1 (SO16)

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	C	D ⁽¹⁾	E (2)	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT403-1		MO-153				99-12-27 03-02-18	

Fig 9. Package outline SOT403-1 (TSSOP16)

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14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT4520_Q100 v.1	20141204	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

16.2 Definitions

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